



Product Overview

NTLJF4156N: Power MOSFET 30V 4.6A 70 mOhm Single N-Channel WDFN-6 FETky

For complete documentation, see the data sheet

Product Description

Power MOSFET and Schottky Diode 30 V, 4.0 A, µCool™ N-Channel, with 2.0 A Schottky Barrier Diode, 2x2 mm WDFN Package

Features

- WDFN Package Provides Exposed Drain Pad for Excellent Thermal Conduction
- Co-Packaged MOSFET and Schottky For Easy Circuit Layout
- $R_{DS(on)}$ Rated at Low $V_{GS}=1.5\text{ V}$
- Low Profile (< 0.8mm) for Easy Fit in Thin Environments
- Low VF Schottky
- This is a Pb-Free Device

Applications

- DC-DC Converters
- Li-Ion Battery Applications in Cell Phones, PDAs, Media Players
- Color Display and Camera Flash Regulators

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	$V_{DS(sat)}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$r_{DS(on)}$ Max @ $V_{GS}=2.5\text{ V}$ (m)	$r_{DS(on)}$ Max @ $V_{GS}=4.5\text{ V}$ (m)	$r_{DS(on)}$ Max @ $V_{GS}=10\text{ V}$ (m)	Q_g Typ @ $V_{GS}=4.5\text{ V}$ (nC)	Q_g Typ @ $V_{GS}=10\text{ V}$ (nC)	Q_{gd} Typ @ $V_{GS}=4.5\text{ V}$ (nC)	Q_{rr} Typ (nC)	C_{iss} Typ (pF)	C_{oss} Typ (pF)	C_{rss} Typ (pF)	Package Type
NTLJF4156NT1G	Pb-free Halide free	Active	N-Channel	with Schottky Diode	30	8	1	4	2.3	90	70		5.4		1.24	5	427	51	32	WDFN-6
NTLJF4156NTAG	Pb-free Halide free	Active	N-Channel	with Schottky Diode	30	8	1	4	2.3	90	70		5.4		1.24	5	427	51	32	WDFN-6

For more information please contact your local sales support at www.onsemi.com

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